

Normally – OFF Silicon Carbide Junction Transistor

V_{DS}	=	600 V
$R_{DS(ON)}$	=	25 m Ω
I_D ($T_C = 25^\circ\text{C}$)	=	100 A
h_{FE} ($T_C = 25^\circ\text{C}$)	=	105

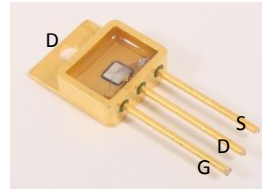
Features

- 225°C maximum operating temperature
- Gate Oxide Free SiC Switch
- Exceptional Safe Operating Area
- Excellent Gain Linearity
- Temperature Independent Switching Performance
- Low Output Capacitance
- Positive Temperature Coefficient of $R_{DS,ON}$
- Suitable for Connecting an Anti-parallel Diode

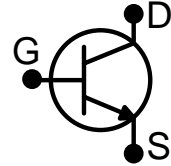
Advantages

- Compatible with Si MOSFET/IGBT Gate Drive ICs
- > 20 μs Short-Circuit Withstand Capability
- Lowest-in-class Conduction Losses
- High Circuit Efficiency
- Minimal Input Signal Distortion
- High Amplifier Bandwidth

Package



TO-258



Applications

- Down Hole Oil Drilling
- Geothermal Instrumentation
- Solenoid Actuators
- General Purpose High-Temperature Switching
- Amplifiers
- Solar Inverters
- Switched-Mode Power Supply (SMPS)
- Power Factor Correction (PFC)

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Section I: Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit	Notes
Drain – Source Voltage	V_{DS}	$V_{GS} = 0\text{ V}$	600	V	
Continuous Drain Current	I_D	$T_J = 225^\circ\text{C}, T_C = 25^\circ\text{C}$	100	A	Fig. 21
Continuous Gate Current	I_{GM}		3.5	A	
Turn-Off Safe Operating Area	RBSOA	$T_J = 225^\circ\text{C}, I_G = 3.5\text{ A},$ Clamped Inductive Load	$I_{D,max} = 50$ @ $V_{DS} \leq V_{DSmax}$	A	Fig. 19
Short Circuit Safe Operating Area	SCSOA	$T_J = 225^\circ\text{C}, I_G = 3.5\text{ A}, V_{DS} = 400\text{ V},$ Non Repetitive	>20	μs	
Reverse Gate – Source Voltage	V_{SG}		30	V	
Reverse Drain – Source Voltage	V_{SD}		25	V	
Power Dissipation	P_{tot}	$T_J = 225^\circ\text{C}, T_C = 25^\circ\text{C}$	769	W	Fig. 16
Operating and Storage Temperature	T_{stg}		-55 to 225	$^\circ\text{C}$	

Section II: Static Electrical Characteristics

Parameter	Symbol	Conditions	Value			Unit	Notes
			Min.	Typical	Max.		
A: On State							
Drain – Source On Resistance	$R_{DS(ON)}$	$I_D = 50\text{ A}, T_j = 25\text{ °C}$		25		mΩ	Fig. 5
		$I_D = 50\text{ A}, T_j = 125\text{ °C}$		39			
		$I_D = 50\text{ A}, T_j = 175\text{ °C}$		43			
		$I_D = 50\text{ A}, T_j = 225\text{ °C}$		62			
Gate – Source Saturation Voltage	$V_{GS,SAT}$	$I_D = 50\text{ A}, I_D/I_G = 40, T_j = 25\text{ °C}$		3.42		V	Fig. 7
		$I_D = 50\text{ A}, I_D/I_G = 30, T_j = 175\text{ °C}$		3.23			
DC Current Gain	h_{FE}	$V_{DS} = 5\text{ V}, I_D = 50\text{ A}, T_j = 25\text{ °C}$		105		–	Fig. 5
		$V_{DS} = 5\text{ V}, I_D = 50\text{ A}, T_j = 125\text{ °C}$		77			
		$V_{DS} = 5\text{ V}, I_D = 50\text{ A}, T_j = 175\text{ °C}$		71			
		$V_{DS} = 5\text{ V}, I_D = 50\text{ A}, T_j = 225\text{ °C}$		69			
B: Off State							
Drain Leakage Current	I_{DSS}	$V_R = 600\text{ V}, V_{GS} = 0\text{ V}, T_j = 25\text{ °C}$		10		μA	Fig. 8
		$V_R = 600\text{ V}, V_{GS} = 0\text{ V}, T_j = 125\text{ °C}$		50			
		$V_R = 600\text{ V}, V_{GS} = 0\text{ V}, T_j = 225\text{ °C}$		100			
Gate Leakage Current	I_{SG}	$V_{SG} = 20\text{ V}, T_j = 25\text{ °C}$		20		nA	
C: Thermal							
Thermal resistance, junction - case	R_{thJC}			0.26		°C/W	Fig. 20

Section III: Dynamic Electrical Characteristics

Parameter	Symbol	Conditions	Value			Unit	Notes
			Min.	Typical	Max.		
A: Capacitance and Gate Charge							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_D = 100\text{ V}, f = 1\text{ MHz}$		6450		pF	Fig. Error! Reference source not found.
Reverse Transfer/Output Capacitance	C_{rss}/C_{oss}	$V_D = 100\text{ V}, f = 1\text{ MHz}$		420		pF	Fig. Error! Reference source not found.
Output Capacitance Stored Energy	E_{OSS}	$V_{GS} = 0\text{ V}, V_D = 400\text{ V}, f = 1\text{ MHz}$		17.4		μJ	Fig. Error! Reference source not found.
Effective Output Capacitance, time related	$C_{oss,tr}$	$I_D = \text{constant}, V_{GS} = 0\text{ V}, V_{DS} = 0...400\text{ V}$		390		pF	
Effective Output Capacitance, energy related	$C_{oss,er}$	$V_{GS} = 0\text{ V}, V_{DS} = 0...400\text{ V}$		284		pF	
Gate-Source Charge	Q_{GS}	$V_{GS} = -5...3\text{ V}$		55		nC	
Gate-Drain Charge	Q_{GD}	$V_{GS} = 0\text{ V}, V_{DS} = 0...400\text{ V}$		156		nC	
Gate Charge - Total	Q_G			211		nC	
B: Switching¹							
Internal Gate Resistance – zero bias	$R_{G(INT-ZERO)}$	$f = 1\text{ MHz}, V_{AC} = 50\text{ mV}, V_{DS} = 0\text{ V}, V_{GS} = 0\text{ V}, T_j = 225\text{ °C}$		0.9		Ω	
Internal Gate Resistance – ON	$R_{G(INT-ON)}$	$V_{GS} > 2.5\text{ V}, V_{DS} = 0\text{ V}, T_j = 225\text{ °C}$		0.09		Ω	
Turn On Delay Time	$t_{d(on)}$			25		ns	
				44			Fig. Error! Reference source not found., Error! Reference source not found.
Fall Time, V_{DS}	t_f	$T_j = 25\text{ °C}, V_{DS} = 400\text{ V}, I_D = 50\text{ A}, \text{Resistive Load}$ Refer to Section V for additional driving information.				ns	
Turn Off Delay Time	$t_{d(off)}$			40		ns	

Rise Time, V_{DS}	t_r	33	ns	Fig. Error! Reference source not found., Error! Reference source not found.
Turn On Delay Time	$t_{d(on)}$	19	ns	
Fall Time, V_{DS}	t_f	43	ns	Fig. Error! Reference source not found.
Turn Off Delay Time	$t_{d(off)}$	89	ns	
Rise Time, V_{DS}	t_r	27	ns	Fig. Error! Reference source not found.
Turn-On Energy Per Pulse	E_{on}	690	μJ	Fig. Error! Reference source not found., Error! Reference source not found.
Turn-Off Energy Per Pulse	E_{off}	359	μJ	Fig. Error! Reference source not found., Error! Reference source not found.
Total Switching Energy	E_{tot}	1049	μJ	
Turn-On Energy Per Pulse	E_{on}	758	μJ	Fig. Error! Reference source not found.
Turn-Off Energy Per Pulse	E_{off}	337	μJ	Fig. Error! Reference source not found.
Total Switching Energy	E_{tot}	1095	μJ	

¹ – All times are relative to the Drain-Source Voltage V_{DS}

Section IV: Figures

A: Static Characteristics

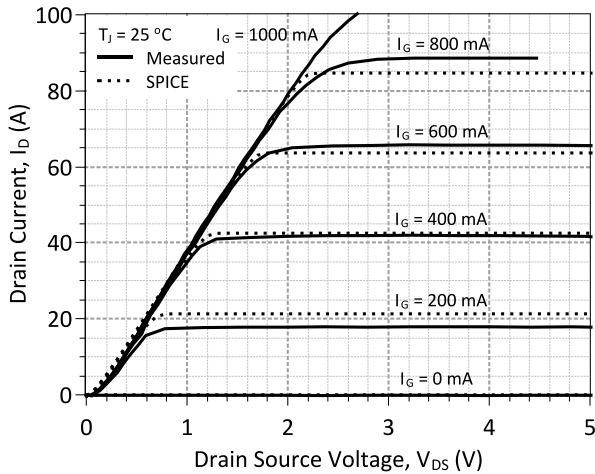


Figure 1: Typical Output Characteristics at 25 °C

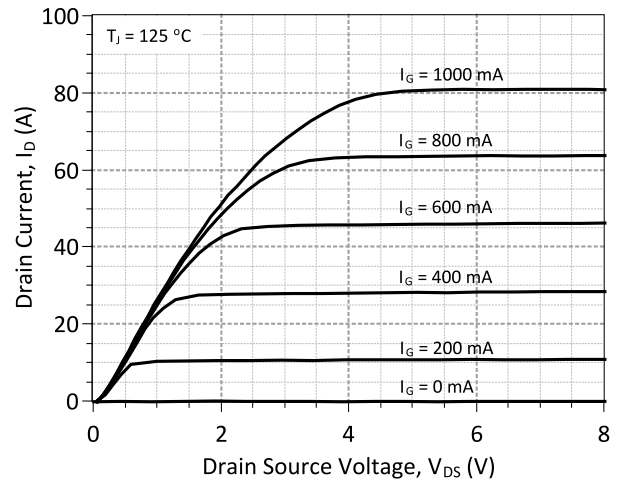


Figure 2: Typical Output Characteristics at 125 °C

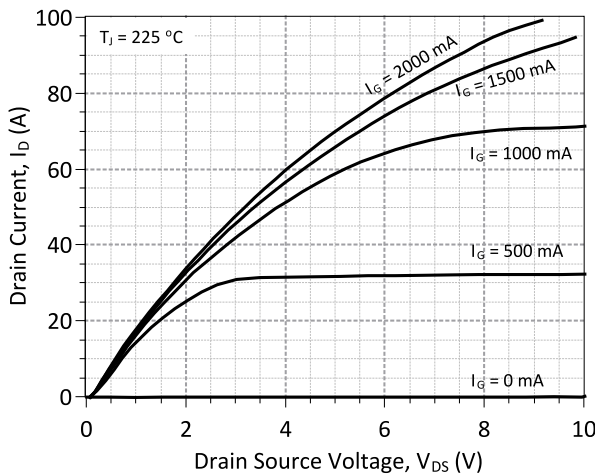


Figure 3: Typical Output Characteristics at 225 °C

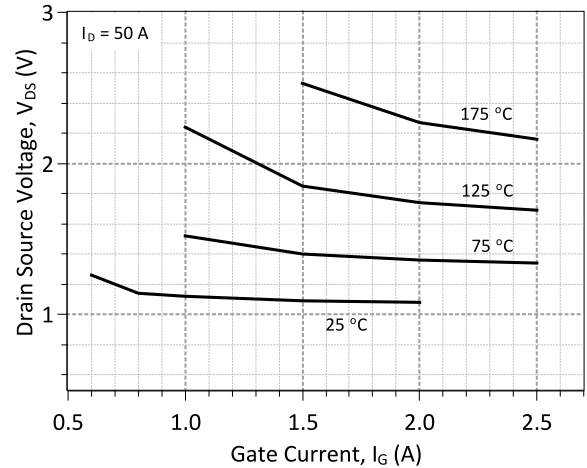


Figure 4: Drain-Source Voltage vs. Gate Current

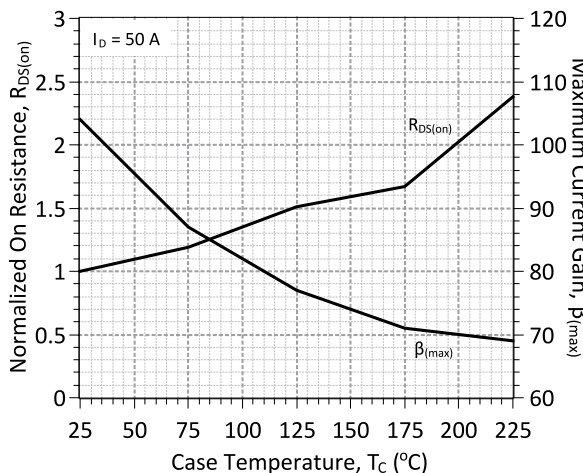


Figure 5: Normalized On-Resistance and Current Gain vs. Temperature

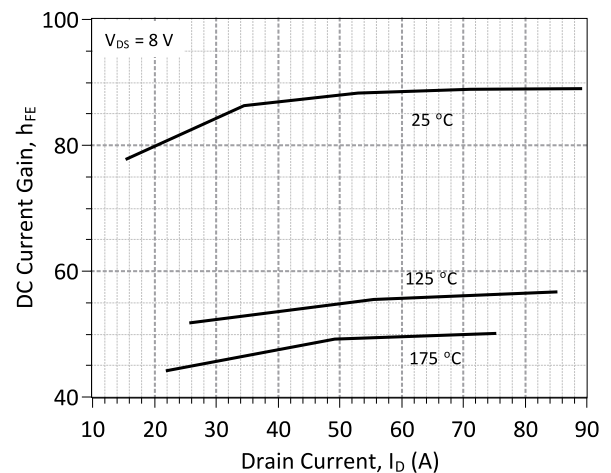


Figure 6: DC Current Gain vs. Drain Current

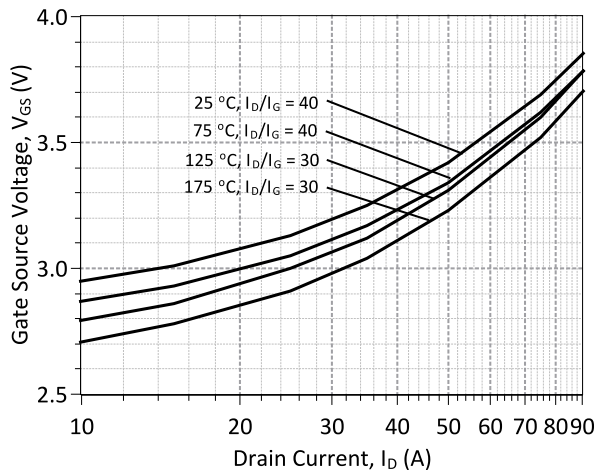


Figure 7: Typical Gate – Source Saturation Voltage

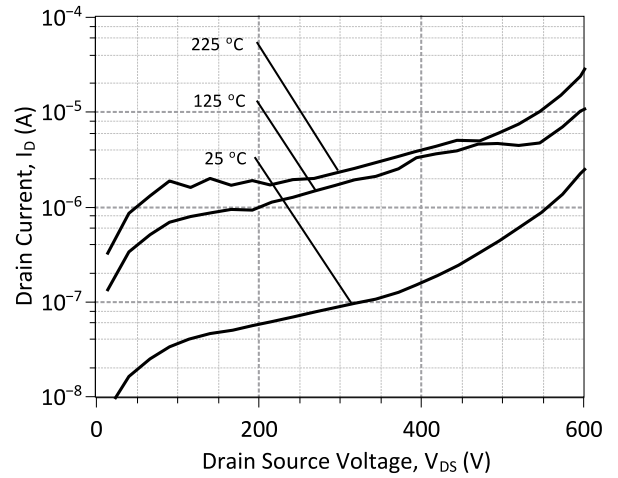


Figure 8: Typical Blocking Characteristics

B: Dynamic Characteristics

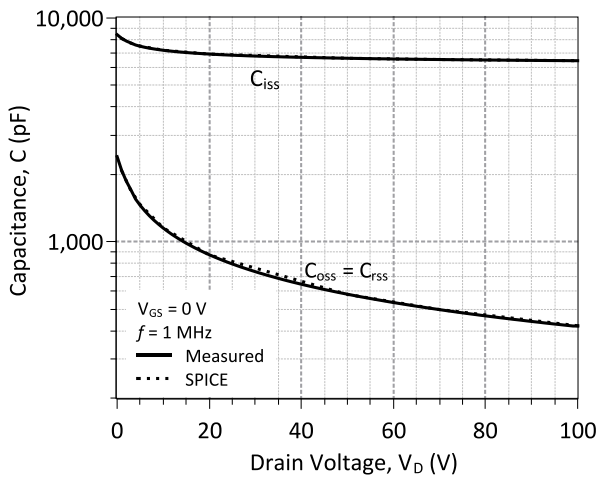


Figure 9: Input, Output, and Reverse Transfer Capacitance

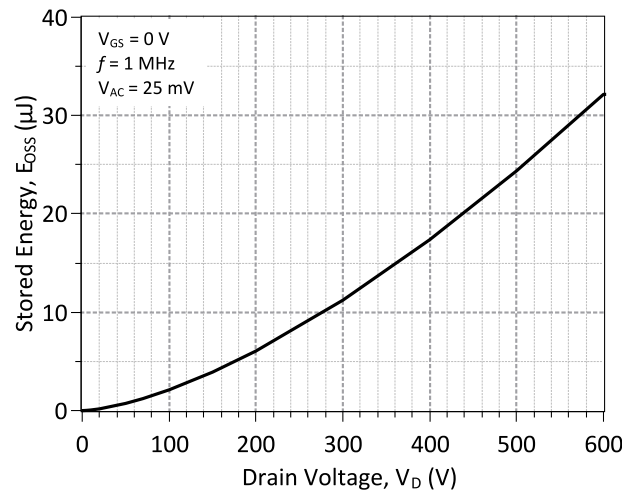


Figure 10: Output Capacitance Stored Energy

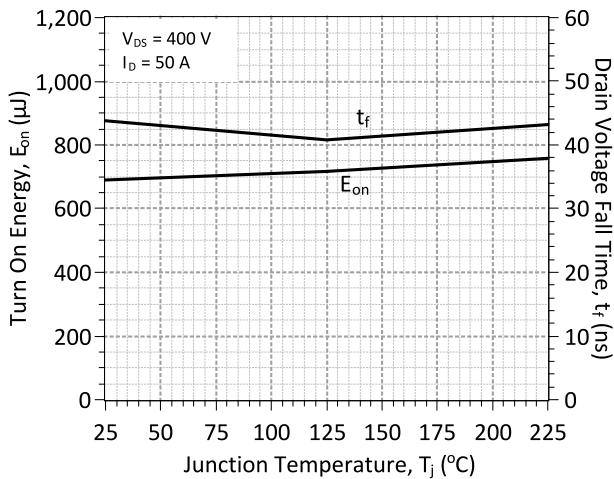


Figure 11: Typical Turn On Energy Losses and Switching Times vs. Temperature

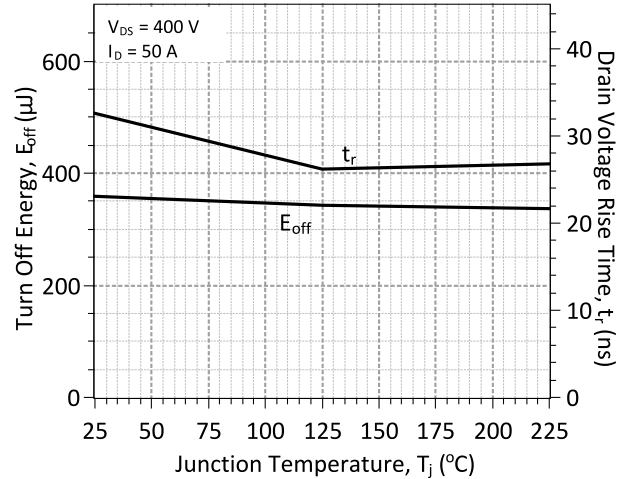


Figure 12: Typical Turn Off Energy Losses and Switching Times vs. Temperature

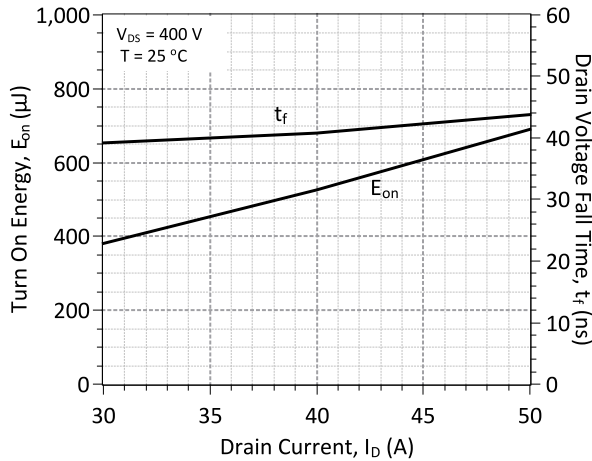


Figure 13: Typical Turn On Energy Losses and Switching Times vs. Drain Current

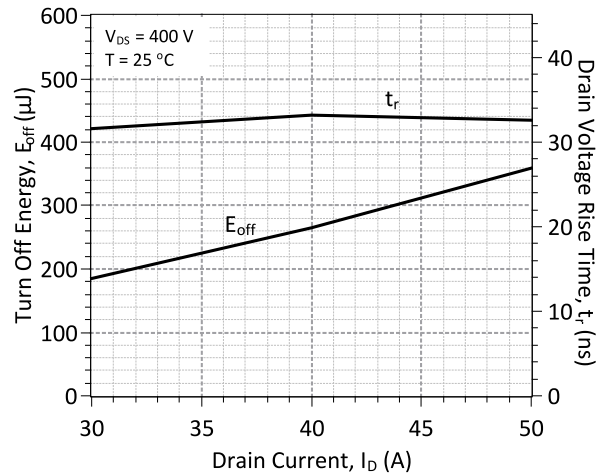


Figure 14: Typical Turn Off Energy Losses and Switching Times vs. Drain Current

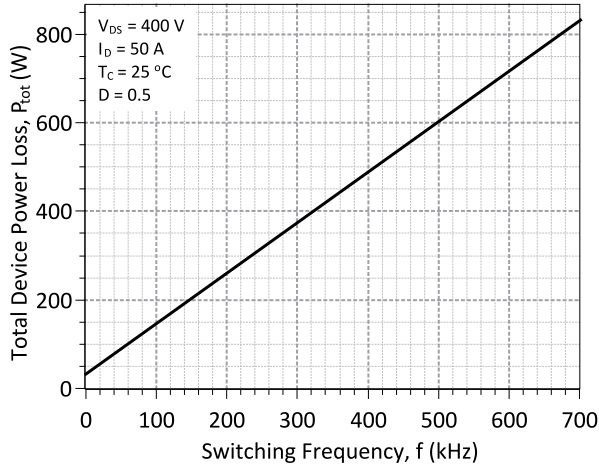


Figure 15: Typical Hard Switched Device Power Loss vs. Switching Frequency²

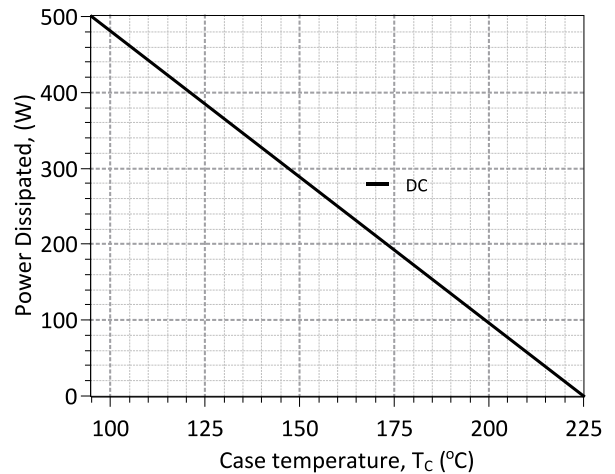


Figure 16: Power Derating Curve

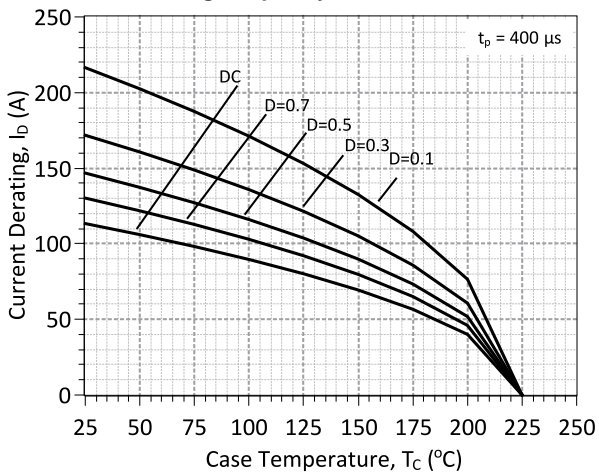


Figure 17: Drain Current Derating vs. Temperature

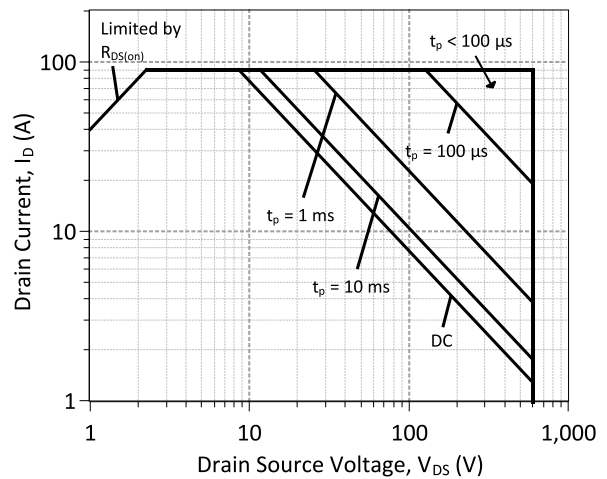


Figure 18: Forward Bias Safe Operating Area at T_c = 25 °C

² – Representative values based on device conduction and switching loss. Actual losses will depend on gate drive conditions, device load, and circuit topology.

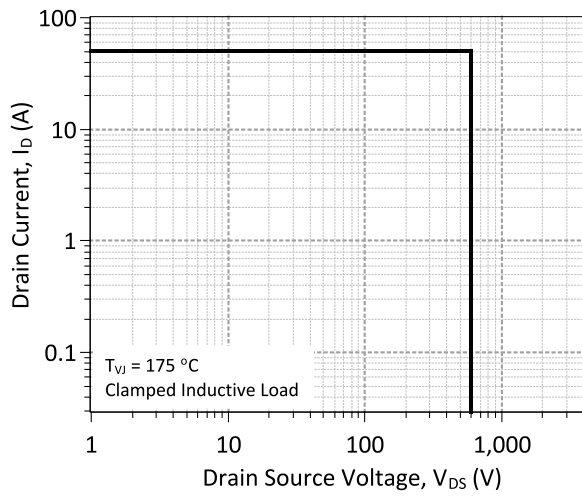


Figure 19: Turn-Off Safe Operating Area

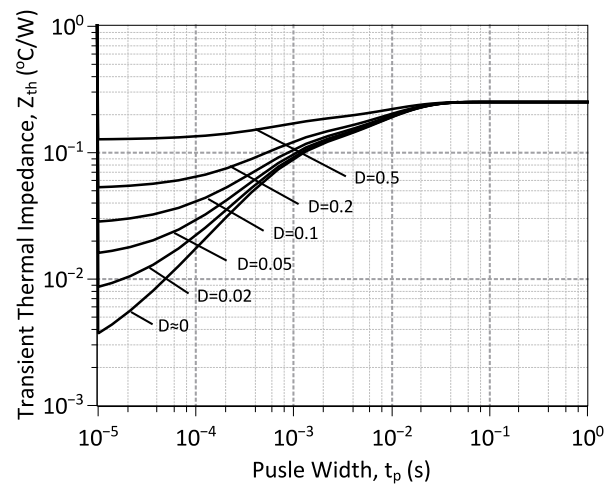


Figure 20: Transient Thermal Impedance

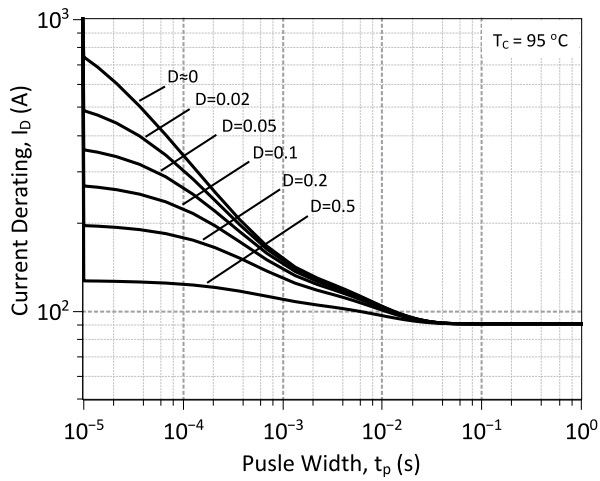


Figure 21: Drain Current Derating vs. Pulse Width

Section V: Driving the GA50JT06-247

The GA50JT06-247 is a current controlled SiC transistor which requires a positive gate current for turn-on and to remain in on-state. It may be driven by different drive topologies depending on the intended application.

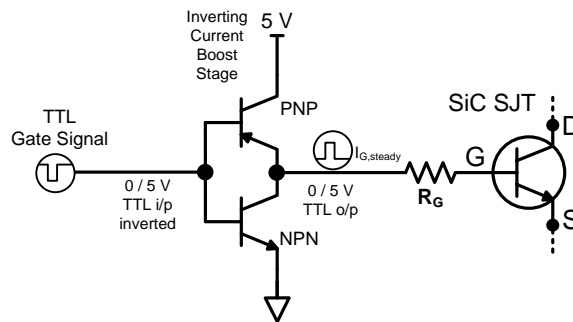
Table 1: Estimated Power Consumption and switching frequencies for various Gate Drive topologies.

Drive Topology	Gate Drive Power Consumption	Switching Frequency
Simple TTL	High	Low
Constant Current	Medium	Medium
High Speed – Boost Capacitor	Medium	High
High Speed – Boost Inductor	Low	High
Proportional	Lowest	Medium
Pulsed Power	Medium	N/A

A: Simple TTL Drive

The GA50JT06-247 may be driven by 5 V TTL logic by using a simple current amplification stage. The current amplifier output current must meet or exceed the steady state gate current, $I_{G,steady}$, required to operate the GA50JT06-247. An external gate resistor R_G , shown in the Figure 22 topology, sets $I_{G,steady}$ to the required level which is dependent on the SJT drain current I_D and DC current gain h_{FE} . R_G may be calculated from the equation below. The values of h_{FE} and $V_{GS,sat}$ may be read from Figure 6 and Figure 7, respectively. $V_{EC,sat}$ can be taken from the PNP datasheet, a partial list of high-temperature PNP and NPN transistors options is given below. High-temperature MOSFETs may also be used in the topology.

$$R_{G,max} = \frac{(5.0\text{ V} - V_{EC,sat}(PNP) - V_{GS,sat}(SJT)) * h_{FE}(T, I_D)}{I_D * 1.5}$$


Figure 22: Simple TTL Gate Drive Topology
Table 2: Partial List of High-Temperature BJTs for TTL Gate Driving

BJT Part Number	Type	$T_{j,max}$ (°C)
PHPT60603PY	PNP	175
PHPT60603NY	NPN	175
2N2222	NPN	200
2N6730	PNP	200
2N2905	PNP	200
2N5883	PNP	200
2N5885	NPN	200

B: High Speed Driving

For ultra high speed GA50JT06-247 switching ($t_r, t_f < 20$ ns) while maintaining low gate drive losses the supplied gate current should include a positive current peak during turn-on, a negative voltage peak during turn-off, and continuous gate current I_G to remain on.

An SJT is rapidly switched from its blocking state to on-state, when the necessary gate charge for turn-on, Q_G , is supplied by a burst of high gate current until the gate-source capacitance, C_{GS} , and gate-drain capacitance, C_{GD} , are fully charged. Ideally, the burst should terminate when the drain voltage has fallen to its on-state value in order to avoid unnecessary drive losses. A negative voltage peak is recommended for the turn-off transition in order to ensure that the gate current is not being supplied under high dV/dt due to the Miller effect. While satisfactory turn off can be achieved with $V_{GS} = 0$ V, a negative V_{GS} value may be used in order to speed up the turn-off transition.

B:1: High Speed, Low Loss Drive with Boost Capacitor

The GA50JT06-247 may be driven using a High Speed, Low Loss Drive with Boost Capacitor topology in which multiple voltage levels, a gate resistor, and a gate capacitor are used to provide current peaks at turn-on and turn-off for fast switching and a continuous gate current while in on-state. As shown in Figure 23, in this topology two gate driver ICs are utilized. An external gate resistor R_G is driven by a low voltage driver to supply the continuous gate current throughout on-state, and a gate capacitor C_G is driven at a higher voltage level to supply a high current peak at turn-on and turn-off. A 3 kV isolated evaluation gate drive board (GA03IDDJT30-FR4) from GeneSiC Semiconductor utilizing this topology is commercially available for high and low-side driving, its datasheet provides additional details about this drive topology.

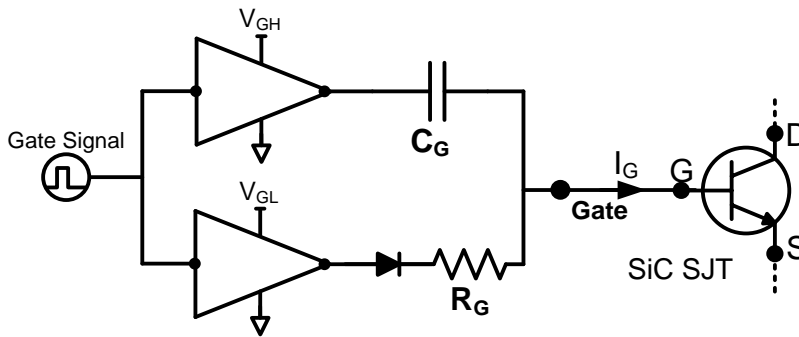


Figure 23: High Speed, Low Loss Drive with Boost Capacitor Topology

B:2: High Speed, Low Loss Drive with Boost Inductor

A High Speed, Low-Loss Driver with Boost Inductor is also capable of driving the GA50JT06-247 at high-speed. It utilizes a gate drive inductor instead of a capacitor to provide the high-current gate current pulses $I_{G,on}$ and $I_{G,off}$. During operation, inductor L is charged to a specified $I_{L,on}$ current value then made to discharge I_L into the SJT gate pin using logic control of $S_1, S_2, S_3,$ and S_4 , as shown in Figure 24. After turn on, while the device remains on the necessary steady state gate current $I_{G,steady}$ is supplied from source V_{CC} through R_G . Please refer to the article "A current-source concept for fast and efficient driving of silicon carbide transistors" by Dr. Jacek Rąbkowski for additional information on this driving topology.³

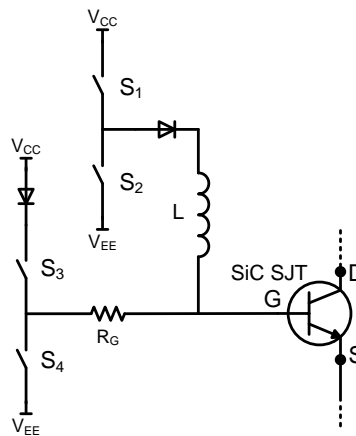


Figure 24: High Speed, Low-Loss Driver with Boost Inductor Topology

³ – Archives of Electrical Engineering. Volume 62, Issue 2, Pages 333–343, ISSN (Print) 0004-0746, DOI: 10.2478/ae-2013-0026, June 2013

C: Proportional Gate Current Driving

A proportional gate drive topology may be beneficial for applications in which the GA50JT06-247 will operate over a wide range of drain current conditions to lower the gate drive power consumption. A proportional gate driver relies on instantaneous drain current I_D feedback to vary the steady state gate current $I_{G,steady}$ supplied to the GA50JT06-247.

C:1: Voltage Controlled Proportional Driver

A voltage controlled proportional driver relies on a gate drive integrated circuit to detect the GA50JT06-247 drain-source voltage V_{DS} during on-state to sense I_D . The integrated circuit will then increase or decrease I_G in response to I_D . This allows I_G and gate drive power consumption to reduce while I_D is low or for I_G to increase when I_D increases. A high voltage diode connected between the drain and sense protects the integrated circuit from high-voltage when blocking. A simplified version of this topology is shown in Figure 25. Additional information will be available in the future at <http://www.genesicsemi.com/references/product-notes/>.

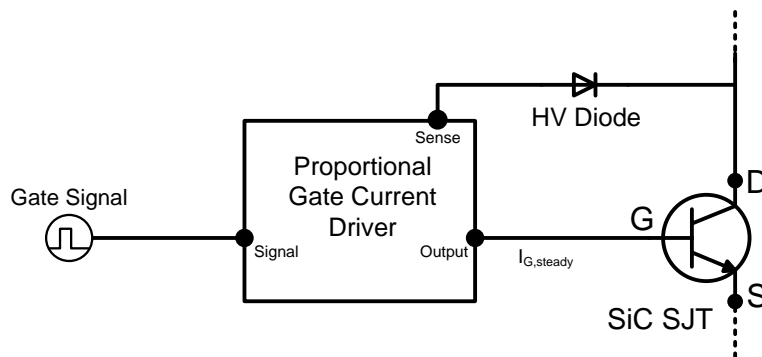


Figure 25: Simplified Voltage Controlled Proportional Driver

C:2: Current Controlled Proportional Driver

The current controlled proportional driver relies on a low-loss transformer in the drain or source path to provide feedback of the GA50JT06-247 drain current during on-state to supply $I_{G,steady}$ into the gate. $I_{G,steady}$ will increase or decrease in response to I_D at a fixed forced current gain which is set by the turns ratio of the transformer, $h_{force} = I_D / I_G = N_2 / N_1$. GA50JT06-247 is initially tuned-on using a gate current pulse supplied into an RC drive circuit to allow I_D current to begin flowing. This topology allows $I_{G,steady}$ and the gate drive power consumption to reduce while I_D is relatively low or for $I_{G,steady}$ to increase when I_D increases. A simplified version of this topology is shown in Figure 26. Additional information will be available in the future at <http://www.genesicsemi.com/references/product-notes/>.

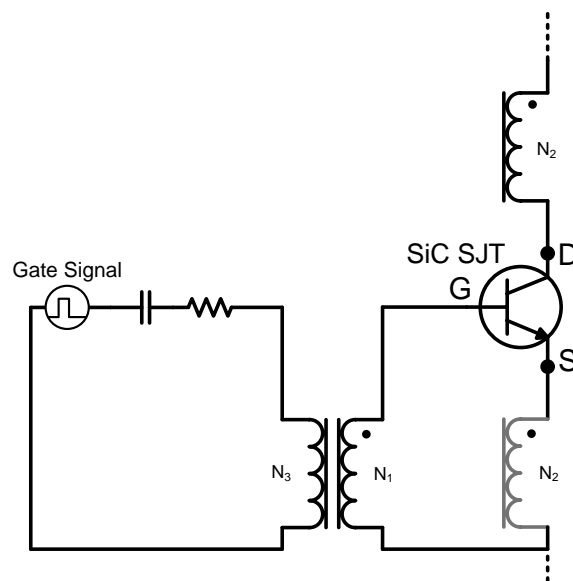
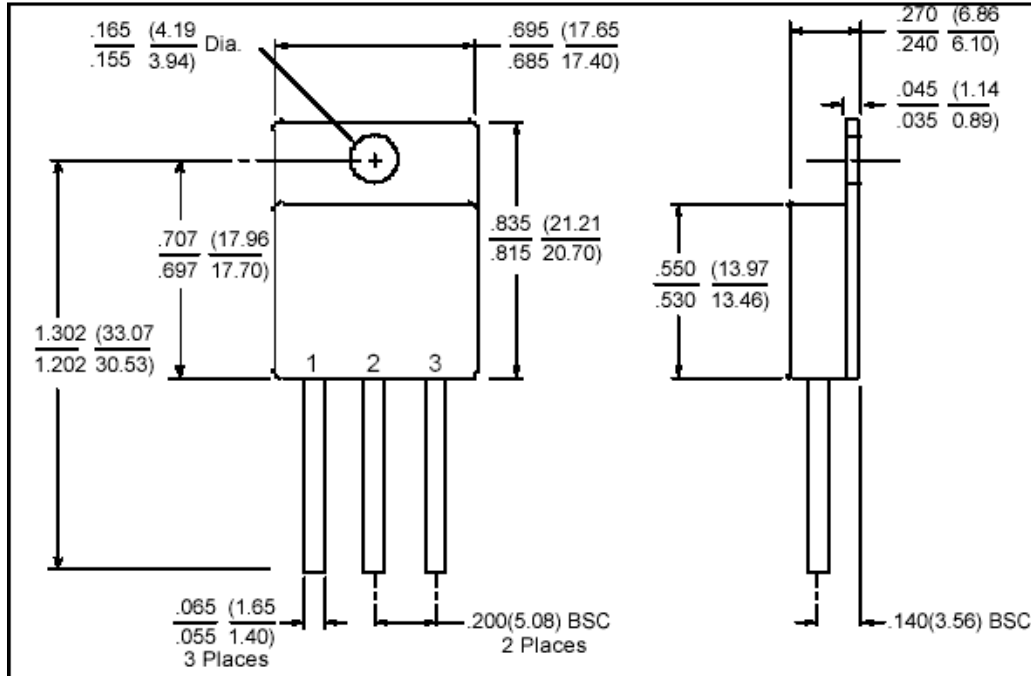


Figure 26: Simplified Current Controlled Proportional Driver

Section VI: Package Dimensions

TO-258 PACKAGE OUTLINE



- NOTE**
1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

Revision History			
Date	Revision	Comments	Supersedes
2014/12/12	5	Updated Electrical Characteristics	
2014/08/23	4	Updated Electrical Characteristics	
2014/04/10	3	Updated Electrical Characteristics	
2014/02/05	2	Updated Electrical Characteristics	
2013/12/19	1	Updated Gate Drive Section	
2013/12/05	0	Initial release	

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Section VII: SPICE Model Parameters

This is a secure document. Please copy this code from the SPICE model PDF file on our website (http://www.genesicsemi.com/images/hit_sic/sjt/GA50JT06-258_SPICE.pdf) into LTSPICE (version 4) software for simulation of the GA50JT06-258.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision: 1.3          $
*      $Date: 12-DEC-2014     $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2014 GeneSiC Semiconductor Inc.
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*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
.model GA50JT06 NPN
*
+ IS          5.00E-47
+ ISE         1.26E-26
+ EG          3.23
+ BF          106
+ BR          0.55
+ IKF         9000
+ NF          1
+ NE          2
+ RB          0.9
+ IRB         0.002
+ RBM         0.09
+ RE          0.01
+ RC          0.013
+ CJC         2.3989E-9
+ VJC         2.8346223
+ MJC         0.4846
+ CJE         6.026E-09
+ VJE         3.17915435
+ MJE         0.52951635
+ XTI         3
+ XTB         -1.2
+ TRC1        7.00E-3
+ VCEO        600
+ ICRATING    100
+ MFG         GeneSiC_Semiconductor
*
* End of GA50JT06 SPICE Model
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